

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	08/903486
Filing Date	July 29, 1997
First Named Inventor	Forbes, Leon
Group Art Unit	2811
Examiner Name	Kang, Donghee

Sheet 1 of 3

NOV 03 2003
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U.S. PATENT & TRADEMARK OFFICE
Attorney Docket No: 303.326US1 Technology Center 2100**US PATENT DOCUMENTS**

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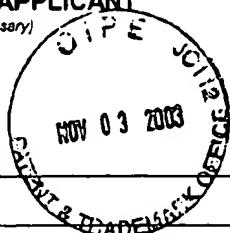
Substitute Disclosure Statement Form (PTO-1440)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 600. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1. Applicant's unique citation designation number (optional); 2. Applicant is to place a check mark here if English language Translation is attached.

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First Named Inventor	Forbes, Leonard	NOV 06 2003
Group Art Unit	2811	
Examiner Name	Kang, Donghee	Technology Center 2100

Sheet 2 of 3

Attorney Docket No: 303.326US1

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Kang, Donghee

DATE CONSIDERED

09-19-04

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		Examiner Name	Kang, Donghee
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Sheet 1 of 1

<i>Complete If Known</i>	
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Examiner Name	Kang, Donghee
Attorney Docket No: 303.326US1	

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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